9012

PNP SILICON TRANSISTOR

TO—92

1.EMITTER

2.BASE

3.COLLECTOR

1 2 3

FEATURES

Power dissipation

P_{CM} : 0.625 W（Tamb=25℃）

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -40 V

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -100 μ A， I_E=0	-40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= -0. 1 mA， I_B=0	-20			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100 μ A， I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40 V I_E=0			-0.1	μ A
Collector cut-off current	I_{CEO}	V_{CE}=- 20 V I_B=0			-0.2	μ A
Emitter cut-off current	I_{EBO}	V_{EB}= - 5 V， I_C=0			-0.1	μ A
DC current gain(note)	$H_{FE\ (1)}$	V_{CE}= -1 V, I_C= -50 mA	64		300	
	$H_{FE\ (2)}$	V_{CE}= -1V, I_C =-500 mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-500 mA, I_B=-50 mA			-0.6	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-500mA,I_B=-50 mA			-1.2	V
Base-emitter voltage	V_{EB}	I_E=-100mA			-1.4	V
Transition frequency	f_T	V_{CE}=- 6 V, I_C= -20 mA f =30MHz	150			MHz

CLASSIFICATION OF $H_{FE(1)}$

Rank	D	E	F	G	H	I
Range	64-91	78-112	96-135	112-166	144-202	190-300

Wing Shing Computer Components Co., (H.K.)Ltd. Tel:(852)2341 9276 Fax:(852)2797 8153
Homepage: http://www.wingshing.com E-mail: ic@wingshing.com